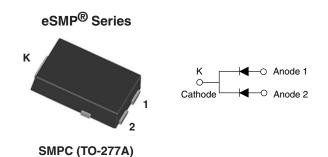
Vishay Semiconductors

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Hyperfast Rectifier, 2 x 4 A FRED Pt[®]



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 4 A				
V _R	100 V				
V _F at I _F	0.72 V				
t _{rr} (typ.)	25 ns				
T _J max.	175 °C				
Package	SMPC (TO-277A)				
Circuit configuration	Common cathode				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		100	V		
Average rectified forward current	per device	I _{F(AV)}	T _{Sp} = 160 °C	8	A		
Average rectilied forward current	per diode			4			
Non-repetitive peak surge current	per device	1	T _J = 25 °C	130			
Non-repetitive peak surge current	per diode	IFSM		70			
Operating junction and storage temp	eratures	T _J , T _{Stg}		-55 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	100	-	-		
Forward voltage, per diode	V	I _F = 4 A	-	0.89	0.95	V	
Forward voltage, per diode	V _F	I _F = 4 A, T _J = 150 °C	-	0.72	0.78		
Reverse leakage current, per diode	I _R	$V_{R} = V_{R}$ rated	-	-	2		
Reverse leakage current, per diode		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	4	80	μA	
Junction capacitance	CT	V _R = 100 V	-	18	-	pF	

Revision: 13-Jan-2021

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Document Number: 95704

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COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ J}$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		25	-		
Povereo recovery time	+	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	25		
Reverse recovery time t _{rr}	۲r	T _J = 25 °C		-	18	-	ns	
		T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs V _B = 160 V	-	27	-		
Peak receivery aurrent		T _J = 25 °C		-	2	-	Α	
Peak recovery current I _R	IRRM	T _J = 125 °C		-	3.6	-	A	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	18	-	nC	
	Qrr	T _J = 125 °C		-	50	-		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to mount, per leg	R _{thJM}		-	2.5	3.5	°C/W
Thermal resistance, junction to ambient, per leg	R _{thJA}		-	80	-	°C/W
Approximate weight			0.1		g	
				0.0035		oz.
Marking device		Case style SMPC (TO-277A)		QC	CH1	

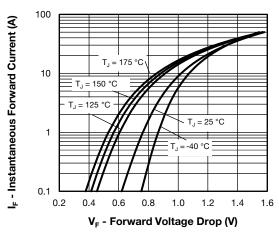


Fig. 1 - Typical Forward Voltage Drop Characteristics

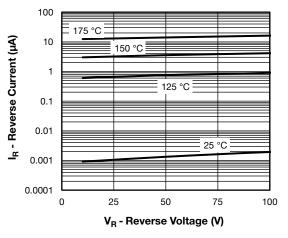
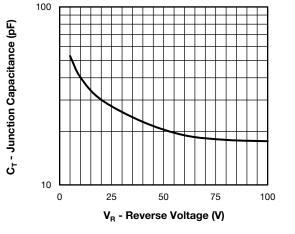


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

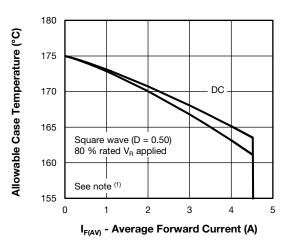


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

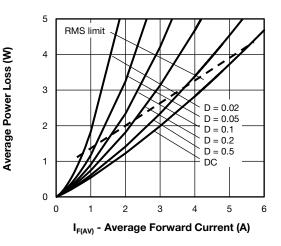


Fig. 5 - Forward Power Loss Characteristics

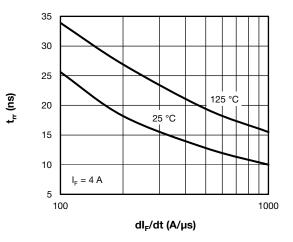


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

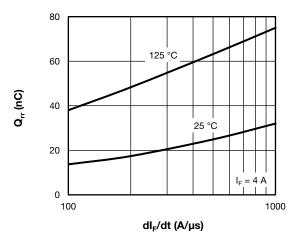


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ at \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ at \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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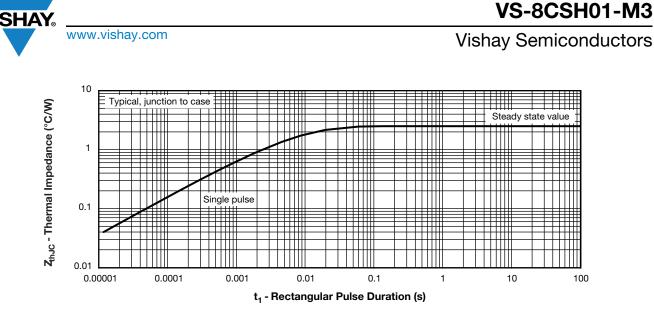


Fig. 8 - Typical Transient Thermal Impedance, Junction to Case

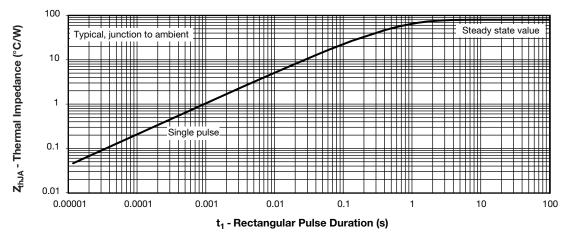


Fig. 9 - Typical Transient Thermal Impedance, Junction to Ambient

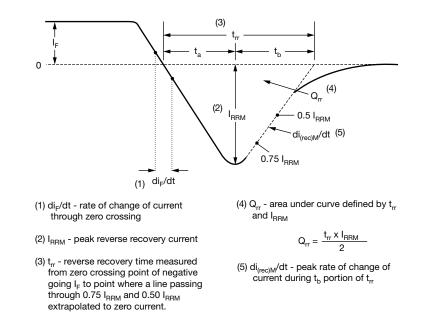


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	8	с	s	н	01	-МЗ
		2	3	4	5	6	7
	1	- Vis	hay Sen	niconduo	ctors pro	oduct	
	2	- Cur	rent rati	ng (8 =	8 A)		
	3	- Circ	cuit conf	iguratio	า:		
		C =	commo	n catho	de		
	4	- S=	SMPC	package	9		
	5	- Pro	cess typ	be,			
		H =	hyper fa	ast reco	very		
	6	- Vol	tage coo	de (01 =	100 V)		
	7	M3	s = halog	gen-free	, RoHS	-complia	ant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-8CSH01-M3/86A	1500	1500	7" diameter plastic tape and reel				
VS-8CSH01-M3/87A	6500	6500	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96095				

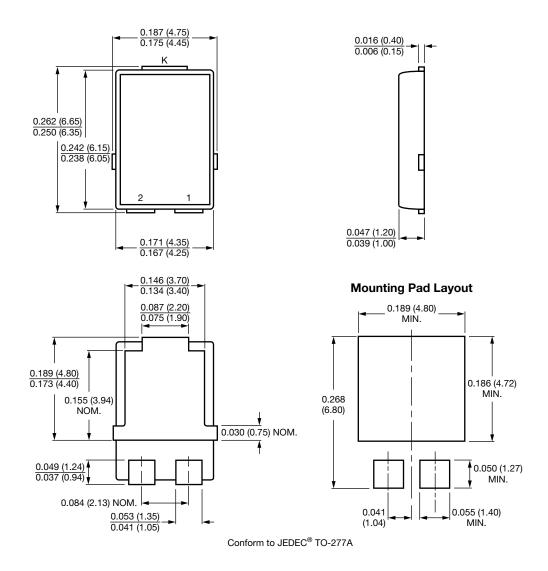
Outline Dimensions





SMPC (TO-277A)

DIMENSIONS in inches (millimeters)





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Revision: 01-Jan-2025

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